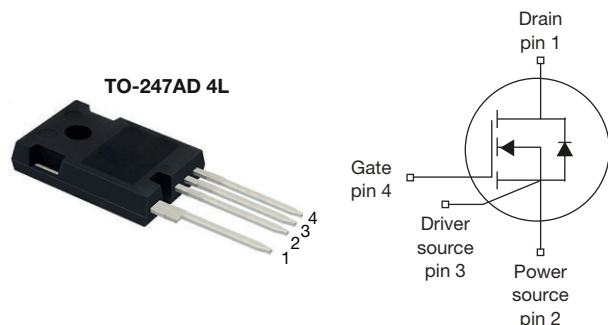


# MaxSiC™ 1200 V N-Channel SiC MOSFET


**Marking Code:** 120A080FL

## FEATURES

- Fast switching speed
- Short circuit withstand time 3  $\mu$ s
- Material categorization:  
for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Charger
- Auxiliary motor drive
- DC/DC converter

## PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	1200	
$R_{DS(on)}$ typ. ( $m\Omega$ ) at 25 °C	$V_{GS} = 20$ V	80
$Q_g$ typ. (nC)	47.3	
$I_D$ (A)	29	
$C_{oss}$ typ. (pF)	50	
$P_D$ (W)	139	
Configuration	Single	

## ORDERING INFORMATION

Package	TO-247AD 4L
Lead (Pb)-free and halogen-free	MXP120A080FL-GE3

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage <sup>a</sup>		V <sub>DS</sub>	1200	V
Gate-source voltage		V <sub>GS</sub>	-10 / +22	
Recommended operation voltage of gate-source		V <sub>GSOP</sub>	-5 / +20	
Continuous drain current	T <sub>C</sub> = 25 °C	I <sub>D</sub>	29	A
	T <sub>C</sub> = 100 °C	I <sub>D</sub>	18	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	58	
Short-circuit withstand time <sup>c</sup>		T <sub>SC</sub>	3	μs
Maximum power dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	139	W
	T <sub>C</sub> = 100 °C	P <sub>D</sub>	56	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering recommendations (peak temperature)	For 10 s		260	°C

## Notes

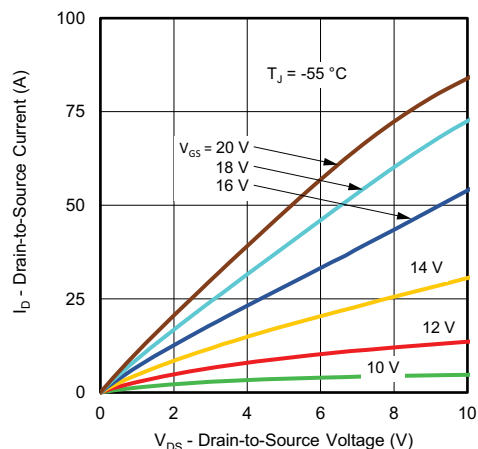
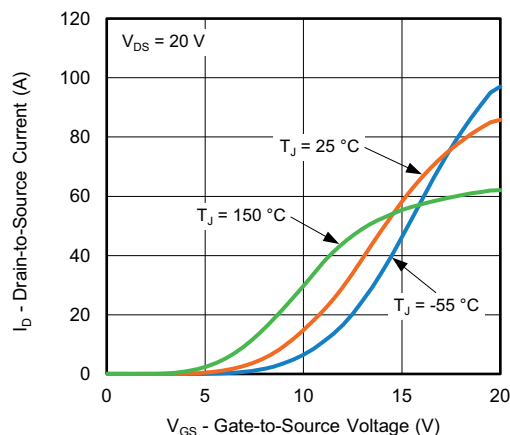
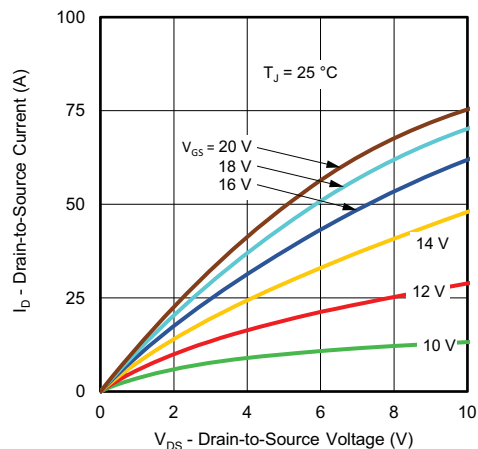
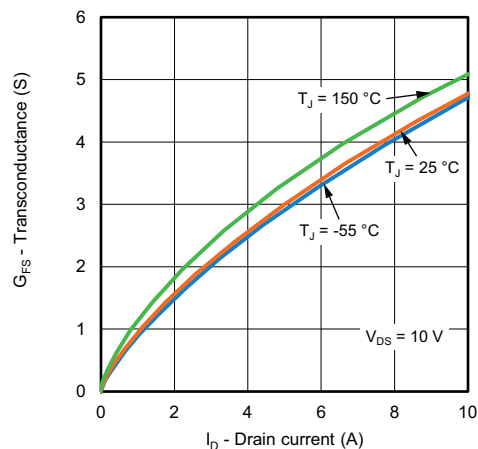
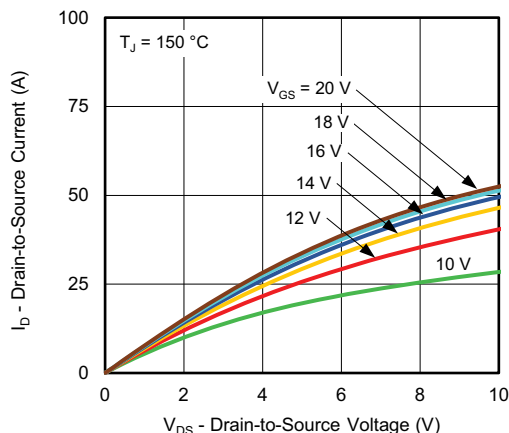
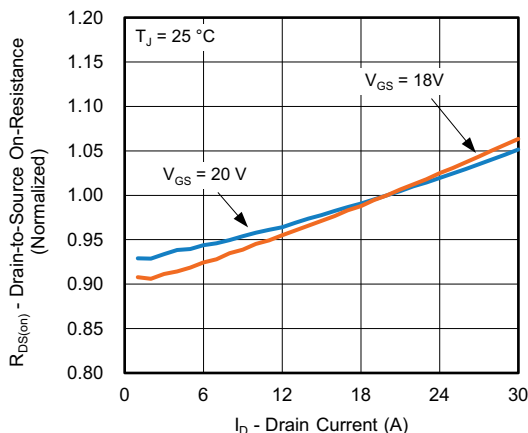
- a.  $T_J = 25$  °C to 150 °C  
b. Repetitive rating; pulse width limited by maximum junction temperature  
c. Verified by the design / characterization

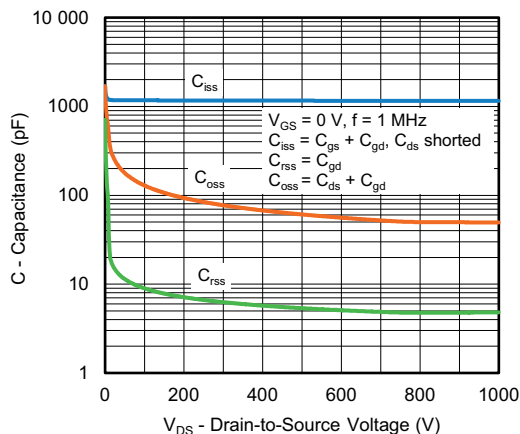
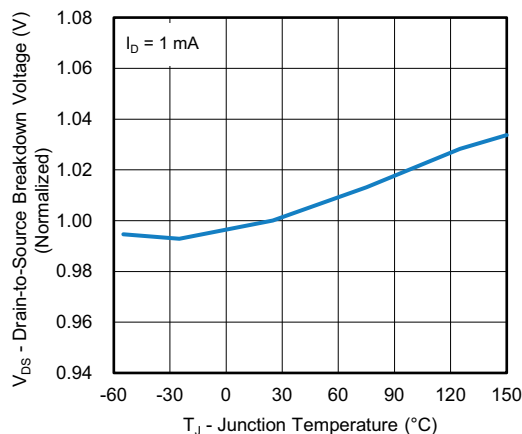
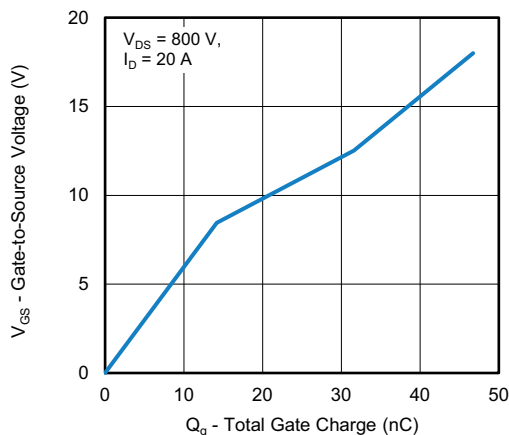
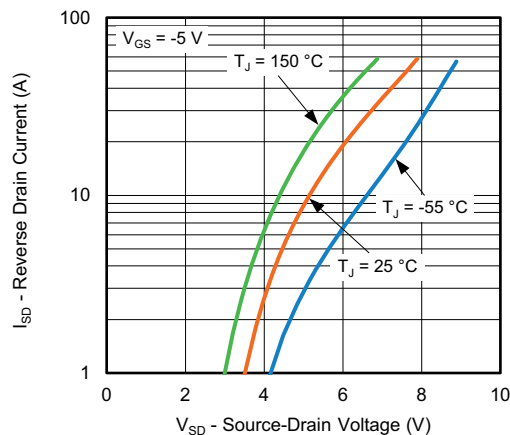
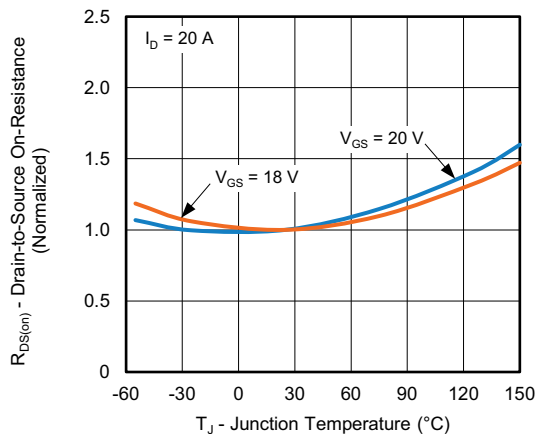
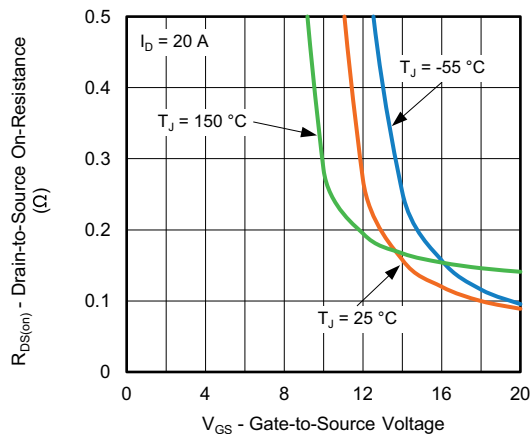
**THERMAL RESISTANCE RATINGS**

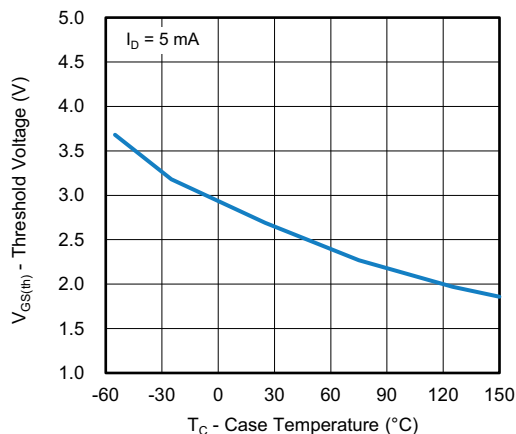
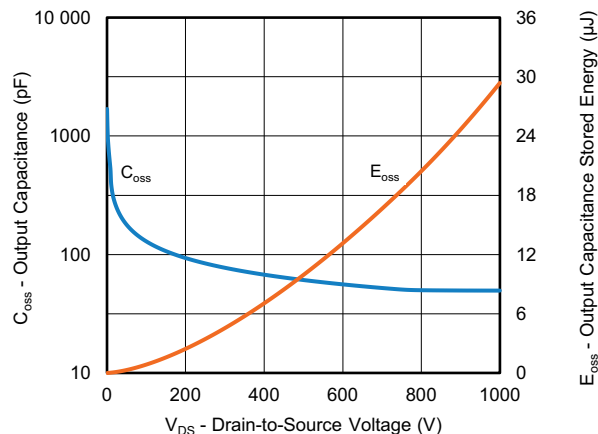
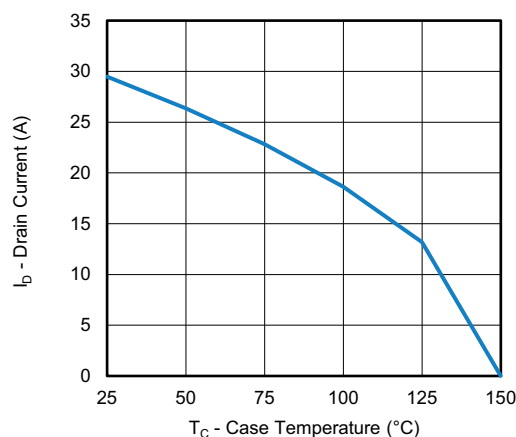
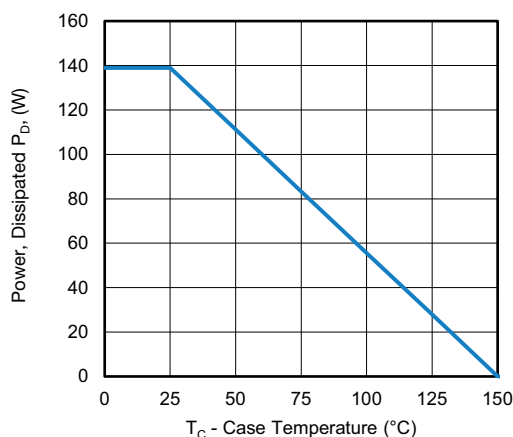
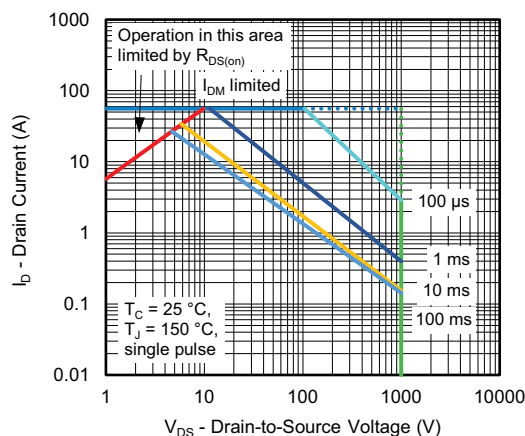
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	40	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	-	0.9	

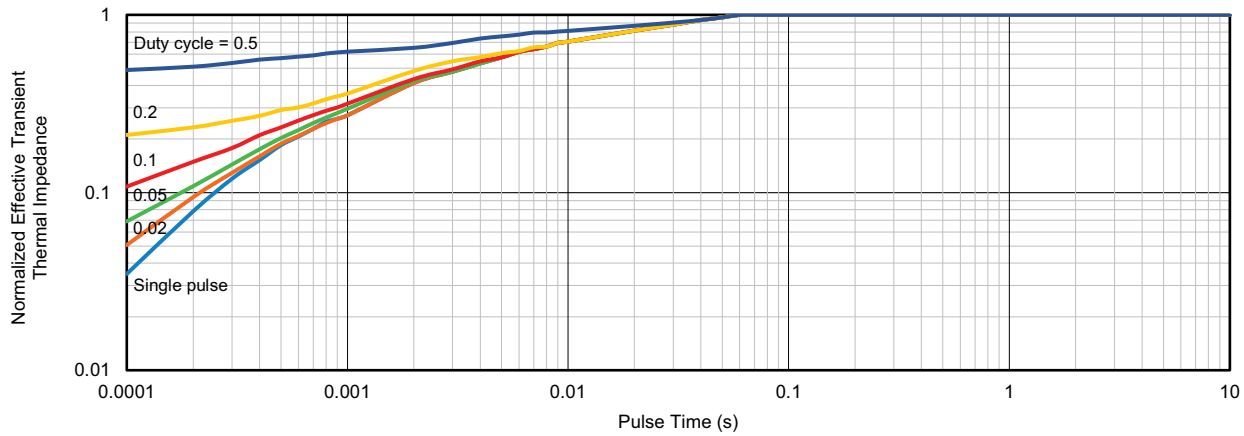
**SPECIFICATIONS** ( $T_J = 25\text{ °C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	1200	-	-	V
Gate-source threshold voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 5 mA	-	2.69	-	V
		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 5 mA, T <sub>J</sub> = 150 °C	-	1.86	-	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>GS</sub> = +22 V, V <sub>DS</sub> = 0 V	-	-	100	nA
		V <sub>GS</sub> = -10 V, V <sub>DS</sub> = 0 V	-	-	-100	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 960 V, V <sub>GS</sub> = 0 V	-	-	10	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 20 V, I <sub>D</sub> = 20 A	-	80	100	mΩ
		V <sub>GS</sub> = 20 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 150 °C	-	128	160	
		V <sub>GS</sub> = 18 V, I <sub>D</sub> = 20 A	-	95	119	
		V <sub>GS</sub> = 18 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 150 °C	-	140	175	
Dynamic						
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 800 V, f = 1 MHz	-	1156	-	pF
Output capacitance	C <sub>oss</sub>		-	50	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	5	-	
Coss Stored Energy	E <sub>oss</sub>		-	20	-	μJ
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> = 18 V, I <sub>D</sub> = 20 A, V <sub>DS</sub> = 800 V	-	47.3	-	nC
Gate-source charge	Q <sub>gs</sub>		-	14.2	-	
Gate-drain charge	Q <sub>gd</sub>		-	17.8	-	
Gate Resistance	R <sub>g</sub>	V <sub>DS</sub> = 0 V, f = 1 MHz	-	9.8	-	Ω
Switching Characteristics						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>GS</sub> = -5 V ~ 18 V, I <sub>D</sub> = 20 A, V <sub>DS</sub> = 800 V, R <sub>g(ext)</sub> = 4.4 Ω	-	13	-	ns
Rise time	t <sub>r</sub>		-	19	-	
Turn-off delay time	t <sub>d(off)</sub>		-	15	-	
Fall time	t <sub>f</sub>		-	8	-	
Turn-on switching energy	E <sub>on</sub>		-	258	-	μJ
Turn-off switching energy	E <sub>off</sub>	-	24	-		
Body Diode Ratings and Characteristic						
Forward diode voltage	V <sub>SD</sub>	V <sub>GS</sub> = -5 V, I <sub>SD</sub> = 10 A, T <sub>J</sub> = 25 °C	-	5.1	-	V
Continuous diode forward current	I <sub>SD</sub>	V <sub>GS</sub> = -5 V, T <sub>J</sub> = 25 °C	-	-	21	A
Pulsed diode forward current	I <sub>SDM</sub>		-	-	58	
Reverse recovery time	t <sub>rr</sub>	V <sub>GS</sub> = -5 V, I <sub>SD</sub> = 20 A, V <sub>R</sub> = 800 V, di/dt = 1000 A/μs	-	14	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	35	-	nC
Reverse recovery current	I <sub>rrm</sub>		-	4.5	-	A

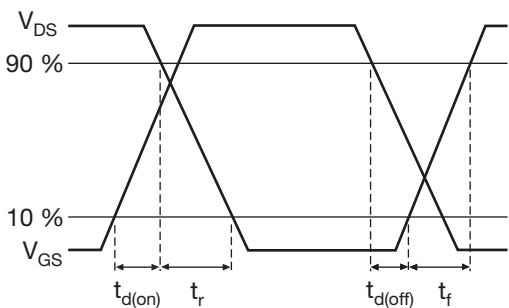
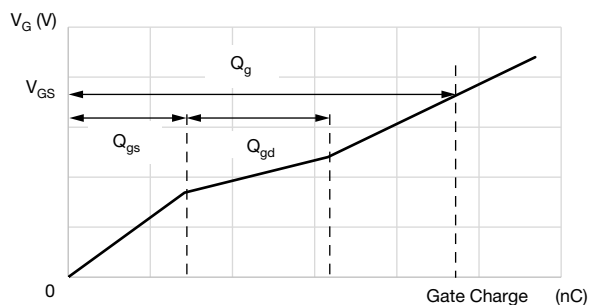
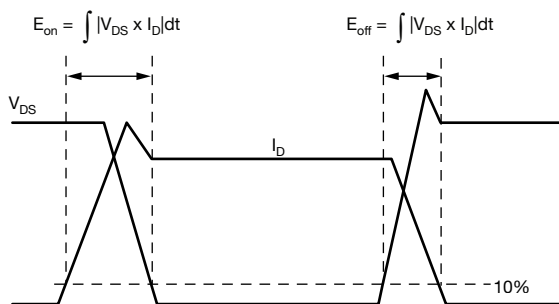
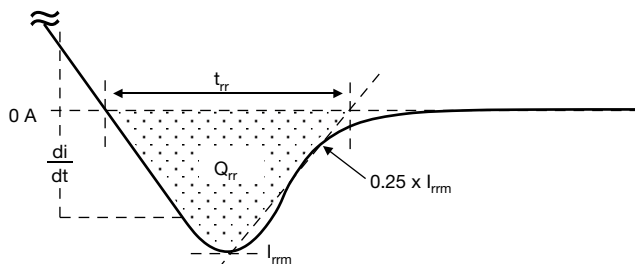
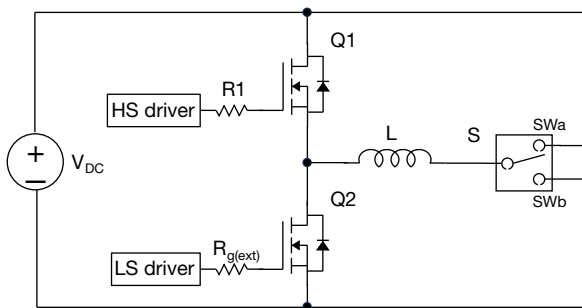
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Typical Transfer Characteristics**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Forward Transconductance vs. Drain Current**

**Fig. 3 - Typical Output Characteristics**

**Fig. 6 - Normalized On-Resistance vs. Drain Current**


**Fig. 7 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 10 - Drain-to-Source Voltage vs. Temperature**

**Fig. 8 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 11 - Typical Source-Drain Diode Forward Voltage**

**Fig. 9 - Normalized On-Resistance vs. Temperature**

**Fig. 12 - On-Resistance vs. Gate-to-Source Voltage**


**Fig. 13 - Threshold Voltage vs. Case Temperature**

**Fig. 15 - Output Capacitances and its Stored Energy vs. Drain-to-Source Voltage**

**Fig. 14 - Drain Current vs. Case Temperature**

**Fig. 16 - Power, Dissipated  $P_D$  vs. Case Temperature**

**Fig. 17 - Safe Operating Area**



**Fig. 18 - Normalized Effective Transient Thermal Impedance**

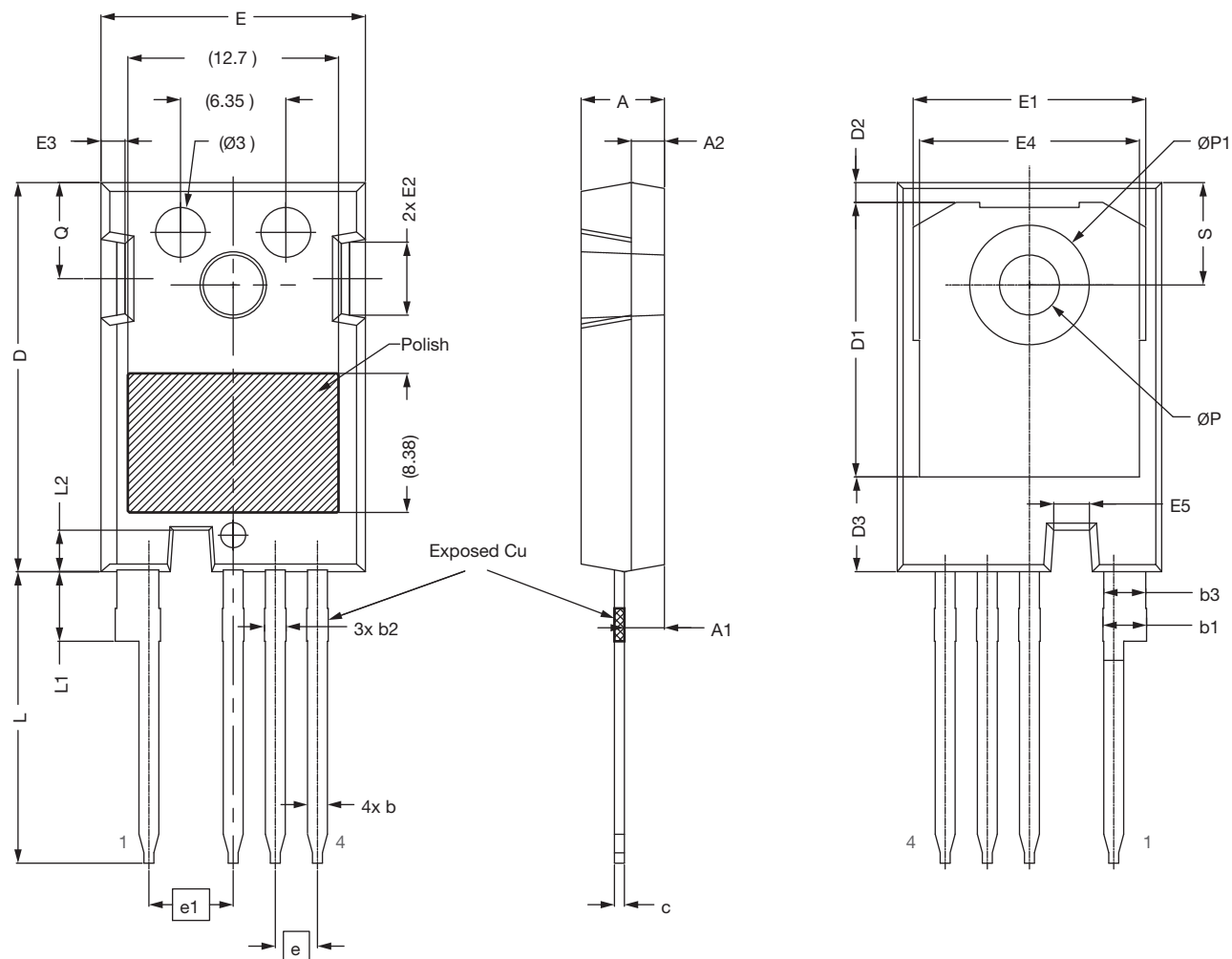

**Fig. 19 - Waveforms of Switching Time**

**Fig. 22 - Waveforms for Gate Charge**

**Fig. 20 - Waveforms for Switching Energy**

**Fig. 23 - Waveforms for Reverse Recovery**

**Fig. 21 - Switching and Reverse Diode Characteristics Measurement Circuit**

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## Case Outline for TO-247AD 4L Package

FACILITY CODE: 9







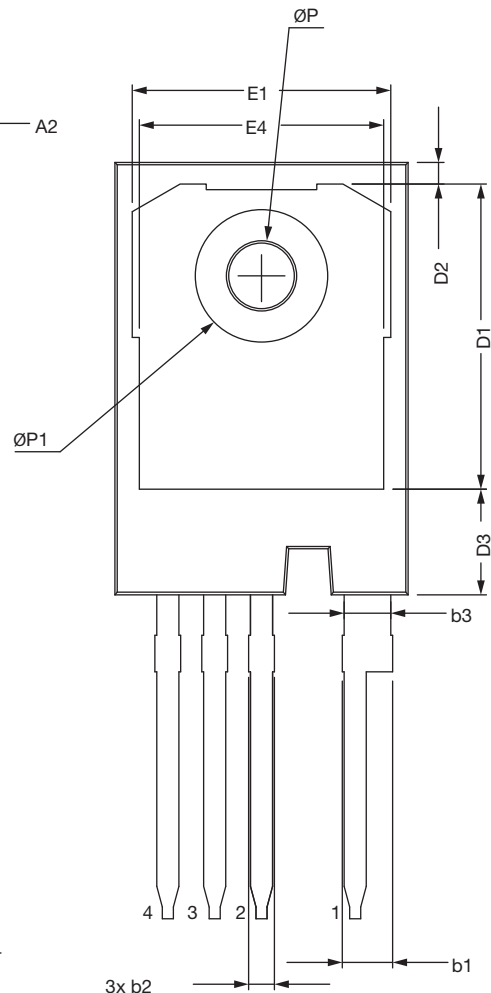
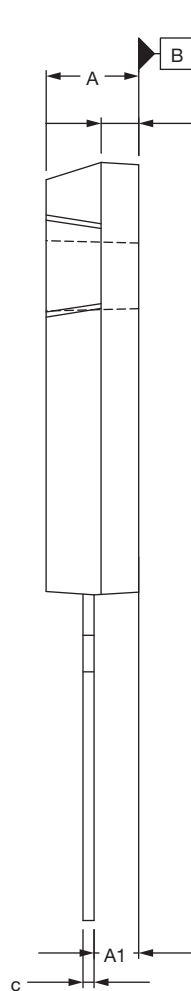
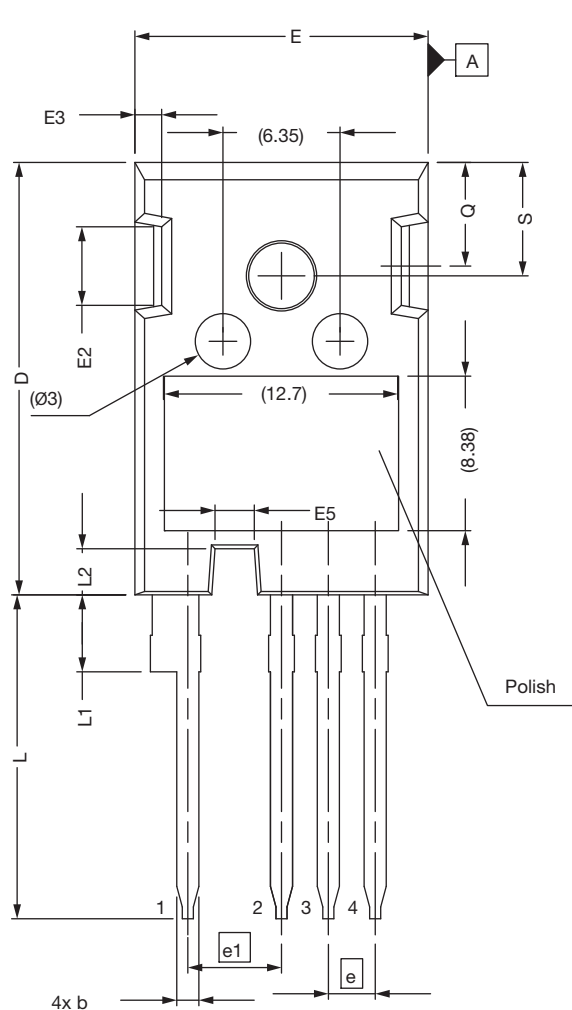
DIM.	MILLIMETERS	
	MIN.	MAX.
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b	1.07	1.33
b1	2.39	2.94
b3	1.07	1.60
c	0.55	0.68
D	23.30	23.60
D1	16.25	17.65
D2	0.95	1.25
E	15.75	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
E5	1.95	2.35
e	2.54 BSC.	
e1	5.08 BSC.	
L	17.31	17.82
L1	3.97	4.37
L2	2.35	2.65
ØP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30

**Notes**

- All dimensions are in mm. Angles are in degrees
- Dimension D and E do not include mold flash.
- All metal surfaces: tin plated, except area of cut
- Dimensioning and toleranceing confirm to ASME Y14.5M-1994
- Creepage 1 is 8.58 mm (ref.) which is the distance alongside the surface between drain (pin 1) and trough the notch towards source (pin 2).  
Creepage 2 is 7.95 mm (ref.) which is the distance from end of the copper slug on the backside of the package to either pin 2, pin 3 or pin 4



FACILITY CODE: N





DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.83	5.02	5.21
A1	2.29	2.41	2.54
A2	1.91	2.00	2.16
b	1.07	1.20	1.33
b1	2.39	2.67	2.94
b2	1.07	1.30	1.60
b3	2.39	2.53	2.69
c	0.55	0.60	0.68
D	23.30	23.45	23.60
D1	16.25	16.55	17.65
D2	0.95	1.19	1.25
D3	5.55	5.71	6.01
E	15.75	15.94	16.13
E1	13.10	14.02	14.15
E2	3.68	4.40	5.10
E3	1.00	1.45	1.90
E4	12.38	13.26	13.43
E5	1.95	2.15	2.35
e	2.54 BSC.		
e1	5.08 BSC.		
L	17.31	17.57	17.82
L1	3.97	4.19	4.37
L2	2.35	2.50	2.65
ØP	3.51	3.61	3.65
ØP1	7.19 ref.		
Q	5.49	5.79	6.00
S	6.04	6.17	6.30
ECN: E24-0559-Rev. B, 11-Nov-2024			
DWG: 6121			

**Notes**

- All dimensions are in mm
- Dimension D and E do not include mold flash.
- Creepage 1 is 8.40 mm (ref.) which is the distance alongside the surface between drain (pin 1) and trough the notch towards source (pin 2).  
Creepage 2 is 7.70 mm (ref.) which is the distance from end of the copper slug on the backside of the package to either pin 2, pin 3 or pin 4



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